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INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	
				Filing Date	
				First Named Inventor	Marius K. Orlowski
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				Examiner Name	
Sheet	1	of	3	Attorney Docket Number	SC12885TP

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. [1]	U.S. Patent Document Number Code [2]	Kind (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Initials*	Cite No. [1]	Foreign Patent Document Office Code [3]	Number [4]	Kind (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T [6]
	AG	WO	00/21118		Marso et al.	04-13-2000		

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
BK	AH	MONFRAY, S. et al; "50nm-Gate All Around (GAA)-Silicon On Nothing (SON)-Devices: A Simple Way to Co-Integration of GAA Transistors Within Bulk MOSFET Process"; 2002 Symposium on VLSI Technology; 2002; pp 108-109; 2002 Symposium on VLSI Technology Digest of Technical Papers	
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